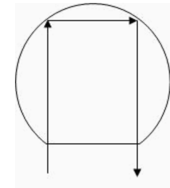
Part Number	Customer

Category		Parameter	Specification	Measurement Method
OverallWafer	1.0	Diameter	150.00 +/- 0.20 mm	
	2.0	Primary Flat Orientation	{110}+/- 0.5 degree	Wafer Vendor
	3.0	Primary Flat Length	57.50 +/- 2.50 mm	Wafer Vendor
	4.0	Secondary Flat Orientation	none	
	5.0	Overall Thickness	327.00 +/- 5.00 µm	ADE, 100%
	6.0	Total Thickness Variation (TTV)	<3.00µm	ADE, 100%
	7.0	Bow	<30.00µm	ADE to ASTM F534, 20%
	8.0	Warp	<30.00µm	ADE to ASTM F657, 20%
	9.0	Edge Chips	None	Bright Light, 100%
	10.0	Edge Exclusion	5mm	
	11.0	Flatness (SBIR)	<1um, 15mm X 15mm. No partials.	
	12.0	Global Flatness (TIR)	<2um	Guaranteed by process
	13.0	Front Surface Quality	Polished	
HandleSilicon	14.0	Handle Silicon Raw Material	Prime Silicon	
	15.0	Handle Growth Method	CZ	Wafer Vendor
	16.0	Handle Orientation	{100} +/- 0.5 degree	Wafer Vendor
	17.0	Handle Thickness	327.00 +/- 5.00 µm	ADE, 100%
	18.0	Handle Doping Type	P	Wafer Vendor
	19.0	Handle Dopant	Boron	Wafer Vendor
	20.0	Handle Resistivity	0.01 ~ 0.02 Ohmcm	Wafer Vendor
	21.0	Backside Finish	Polished, with lasermarking. Light handling scrtaches.	Guaranteed by process
	22.0	Surface Haze	none	Bright Light, 100% (note 2)

Part Number	Customer		
Category	**Parameter**	**Specification**	**Measurement Method**
Shipping Details	Wafer per box :	Max 25	
	Packaging :	Taped Polypropylene Wafer Box Empak, Ultrapak, 150.00mm Antistatic Double Bagging	
	Lot Shipment Data	Device Thickness Bow / Warp Data Handle and SOI Thickness	

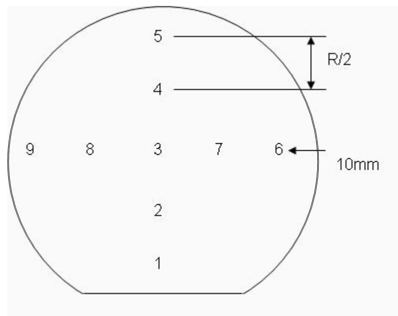
Explanatory Notes

1. Microscope inspection performed using microscope scan as below. 5x objective.



2. All bright light inspections performed exclude all wafer area outside the edge exclusion defined in Overall Wafer, Edge Exclusion. High intensity bright lamp inspection as per ASTM F523.

3. 9 point measurement are as shown in the diagram below:



Additional Information